



Is Now Part of



ON Semiconductor®

To learn more about ON Semiconductor, please visit our website at
www.onsemi.com

Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (_), the underscore (_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.onsemi.com. Please email any questions regarding the system integration to Fairchild_questions@onsemi.com.

ON Semiconductor and the ON Semiconductor logo are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.



FDBL0150N80

N-Channel PowerTrench[®] MOSFET

80 V, 300 A, 1.4 mΩ

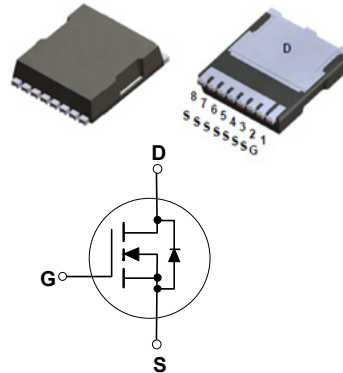
July 2016

Features

- Typical $R_{DS(on)}$ = 1.1 mΩ at V_{GS} = 10V, I_D = 80 A
- Typical $Q_{g(tot)}$ = 172 nC at V_{GS} = 10V, I_D = 80 A
- UIS Capability
- RoHS Compliant

Applications

- Industrial Motor Drive
- Industrial Power Supply
- Industrial Automation
- Battery Operated tools
- Battery Protection
- Solar Inverters
- UPS and Energy Inverters
- Energy Storage
- Load Switch



For current package drawing, please refer to the Fairchild website at https://www.fairchildsemi.com/evaluate/package-specifications/packageDetails.html?id=PN_PSOFA-008

MOSFET Maximum Ratings $T_J = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Ratings	Units
V_{DSS}	Drain-to-Source Voltage	80	V
V_{GS}	Gate-to-Source Voltage	±20	V
I_D	Drain Current - Continuous ($V_{GS}=10$) (Note 1)	$T_C = 25^\circ\text{C}$	A
	Pulsed Drain Current	$T_C = 25^\circ\text{C}$	
E_{AS}	Single Pulse Avalanche Energy (Note 2)	820	mJ
P_D	Power Dissipation	429	W
	Derate Above 25°C	2.86	W/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Temperature	-55 to + 175	$^\circ\text{C}$
$R_{\theta JC}$	Thermal Resistance, Junction to Case	0.35	$^\circ\text{C/W}$
$R_{\theta JA}$	Maximum Thermal Resistance, Junction to Ambient (Note 3)	43	$^\circ\text{C/W}$

Notes:

- 1: Current is limited by bondwire configuration.
- 2: Starting $T_J = 25^\circ\text{C}$, $L = 0.4\text{mH}$, $I_{AS} = 64\text{A}$, $V_{DD} = 40\text{V}$ during inductor charging and $V_{DD} = 0\text{V}$ during time in avalanche.
- 3: $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance, where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design, while $R_{\theta JA}$ is determined by the board design. The maximum rating presented here is based on mounting on a 1 in² pad of 2oz copper.

Package Marking and Ordering Information

Device Marking	Device	Package			
FDBL0150N80	FDBL0150N80	MO-299A	-	-	-

Electrical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
--------	-----------	-----------------	------	------	------	-------

Off Characteristics

$B_{V_{DS}}$	Drain-to-Source Breakdown Voltage	$I_D = 250\mu\text{A}$, $V_{GS} = 0\text{V}$	80	-	-	V
I_{DSS}	Drain-to-Source Leakage Current	$V_{DS} = 80\text{V}$, $T_J = 25^\circ\text{C}$ $V_{GS} = 0\text{V}$, $T_J = 175^\circ\text{C}$ (Note 4)	-	-	1	μA
I_{GSS}	Gate-to-Source Leakage Current	$V_{GS} = \pm 20\text{V}$	-	-	± 100	nA

On Characteristics

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 250\mu\text{A}$	2.0	3.0	4.0	V
$R_{DS(on)}$	Drain to Source On Resistance	$I_D = 80\text{A}$, $T_J = 25^\circ\text{C}$ $V_{GS} = 10\text{V}$, $T_J = 175^\circ\text{C}$ (Note 4)	-	1.1	1.4	$\text{m}\Omega$
			-	2.4	3.1	$\text{m}\Omega$

Dynamic Characteristics

C _{iss}	Input Capacitance	V _{DS} = 25V, V _{GS} = 0V, f = 1MHz		-	12800	-	pF
C _{oss}	Output Capacitance			-	1925	-	pF
C _{rss}	Reverse Transfer Capacitance			-	139	-	pF
R _g	Gate Resistance	f = 1MHz		-	3.0	4.6	Ω
Q _{g(ToT)}	Total Gate Charge at 10V	V _{GS} = 0 to 10V	V _{DD} = 64V I _D = 80A	-	172	188	nC
Q _{g(th)}	Threshold Gate Charge	V _{GS} = 0 to 2V		-	23	27	nC
Q _{gs}	Gate-to-Source Gate Charge			-	51	-	nC
Q _{gd}	Gate-to-Drain “Miller” Charge			-	34	-	nC

Switching Characteristics

t_{on}	Turn-On Time	$V_{DD} = 40\text{V}$, $I_D = 80\text{A}$, $V_{GS} = 10\text{V}$, $R_{GEN} = 6\Omega$	-	-	128	ns
$t_{d(on)}$	Turn-On Delay		-	42	-	ns
t_r	Rise Time		-	73	-	ns
$t_{d(off)}$	Turn-Off Delay		-	87	-	ns
t_f	Fall Time		-	48	-	ns
t_{off}	Turn-Off Time		-	-	193	ns

Drain-Source Diode Characteristics

V_{SD}	Source-to-Drain Diode Voltage	$I_{SD} = 80\text{A}$, $V_{GS} = 0\text{V}$	-	-	1.25	V
		$I_{SD} = 40\text{A}$, $V_{GS} = 0\text{V}$	-	-	1.2	V
t_{rr}	Reverse-Recovery Time	$I_F = 80\text{A}$, $dI_{SD}/dt = 100\text{A}/\mu\text{s}$, $V_{DD} = 64\text{V}$	-	117	136	ns
Q_{rr}	Reverse-Recovery Charge		-	205	269	nC

Note:

4: The maximum value is specified by design at $T_J = 175^\circ\text{C}$. Product is not tested to this condition in production.

Typical Characteristics

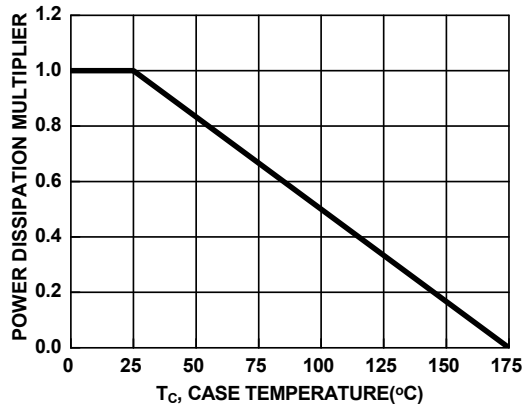


Figure 1. Normalized Power Dissipation vs. Case Temperature

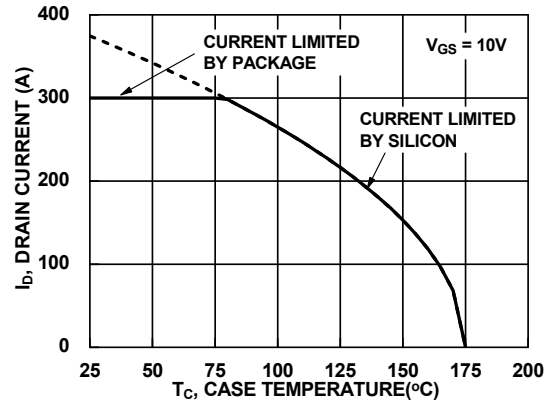


Figure 2. Maximum Continuous Drain Current vs. Case Temperature

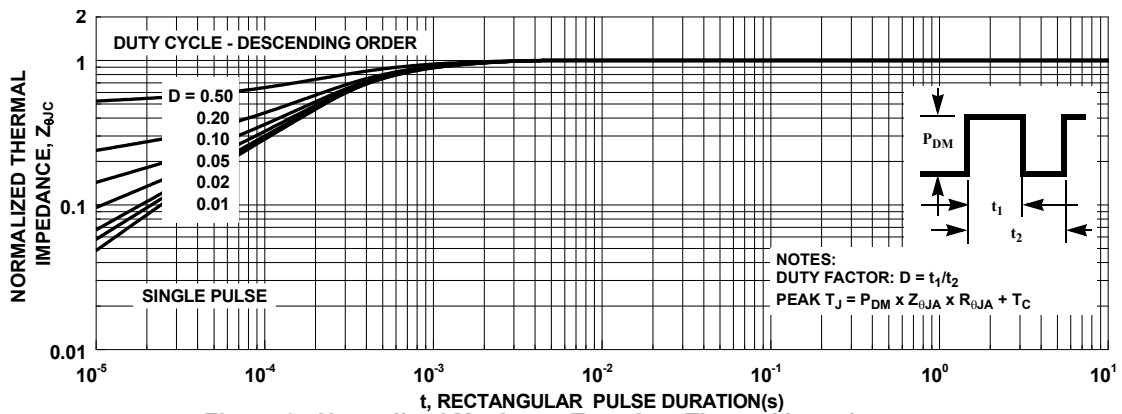


Figure 3. Normalized Maximum Transient Thermal Impedance

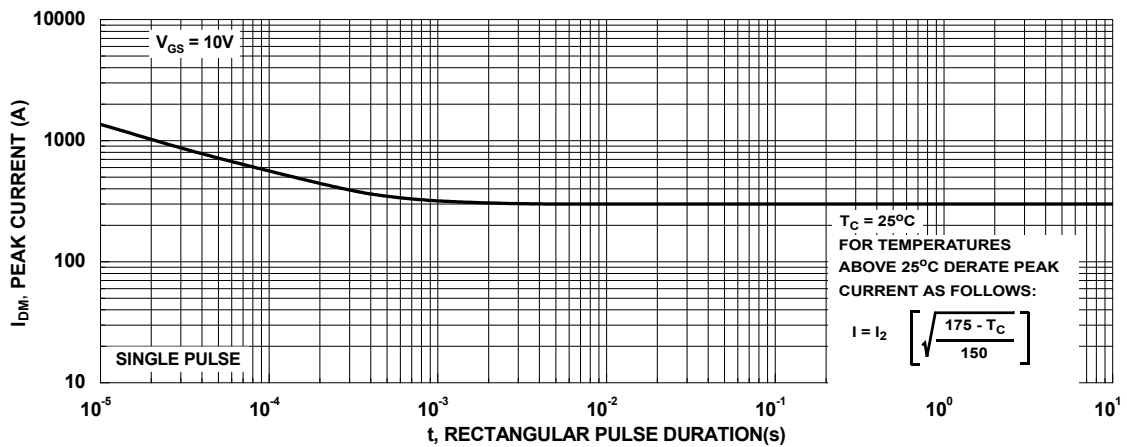


Figure 4. Peak Current Capability

Typical Characteristics

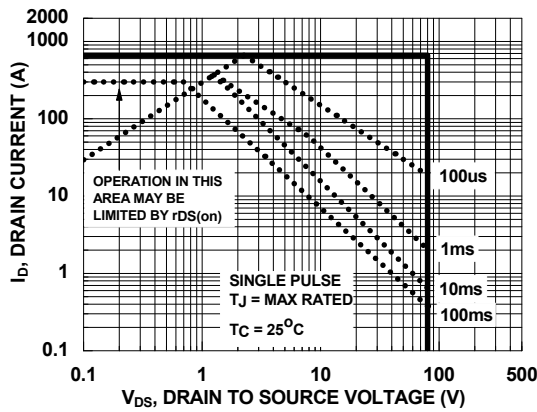
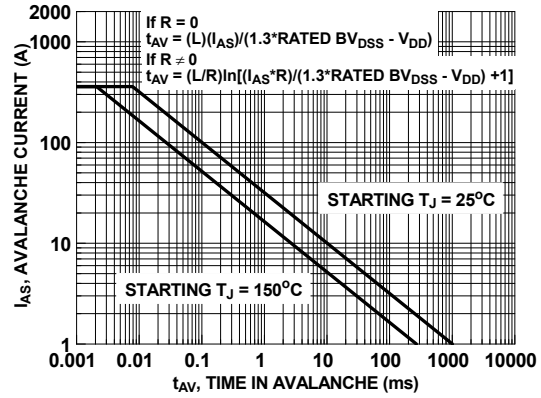


Figure 5. Forward Bias Safe Operating Area



NOTE: Refer to Fairchild Application Notes AN7514 and AN7515

Figure 6. Unclamped Inductive Switching Capability

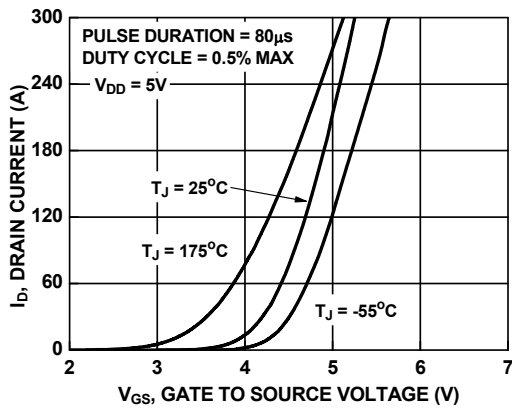


Figure 7. Transfer Characteristics

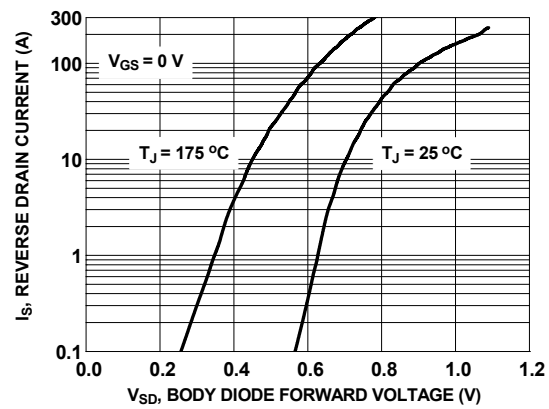


Figure 8. Forward Diode Characteristics

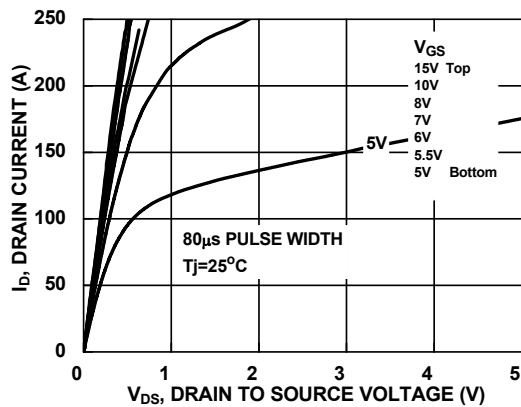


Figure 9. Saturation Characteristics

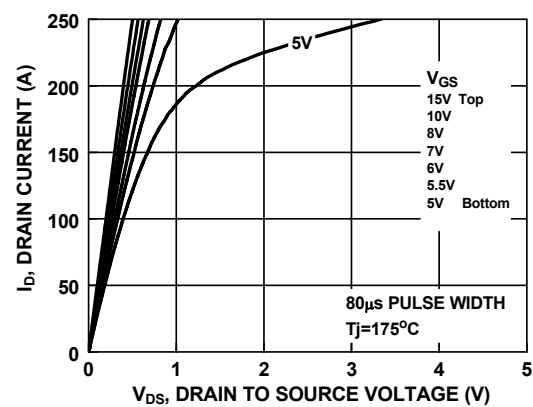


Figure 10. Saturation Characteristics

Typical Characteristics

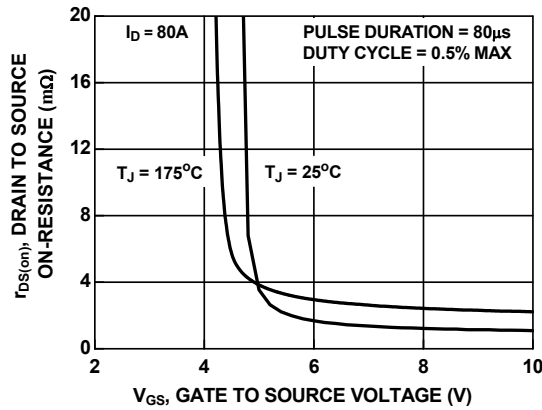


Figure 11. $R_{DS(on)}$ vs. Gate Voltage

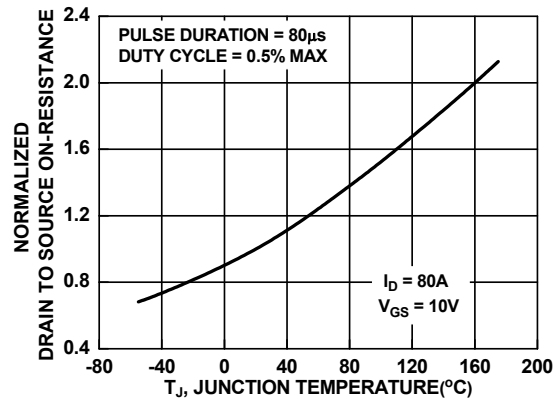


Figure 12. Normalized $R_{DS(on)}$ vs. Junction Temperature

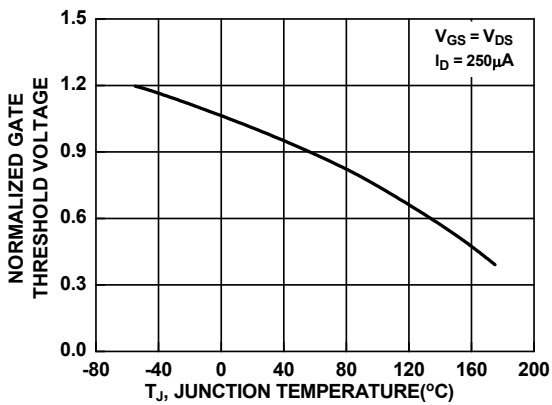


Figure 13. Normalized Gate Threshold Voltage vs. Temperature

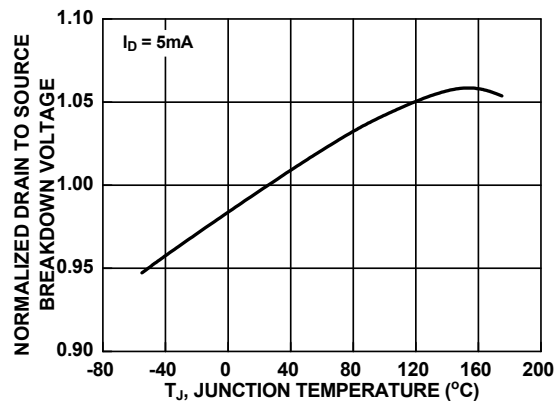


Figure 14. Normalized Drain to Source Breakdown Voltage vs. Junction Temperature

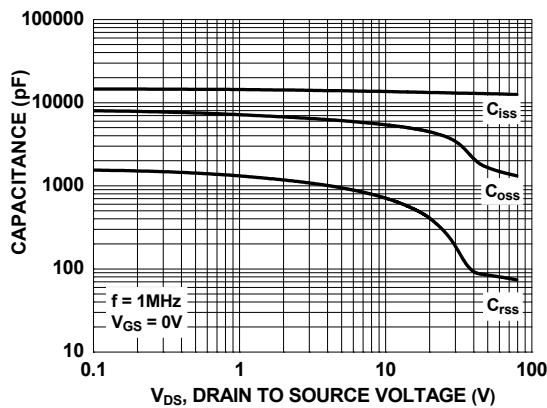


Figure 15. Capacitance vs. Drain to Source Voltage

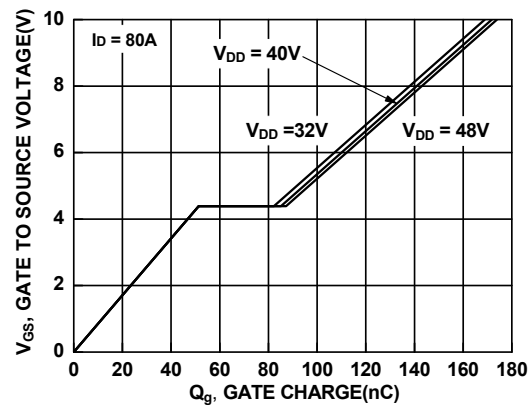
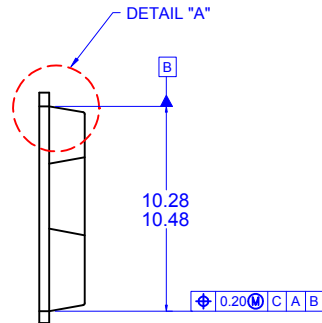
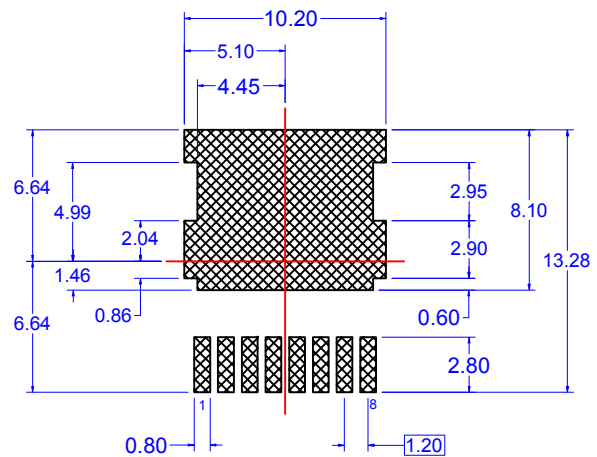


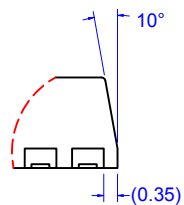
Figure 16. Gate Charge vs. Gate to Source Voltage



DETAIL "A"



LAND PATTERN RECOMMENDATION



DETAIL "B"

NOTES: UNLESS OTHERWISE SPECIFIED

- A) PACKAGE STANDARD REFERENCE:
JEDEC MO-299, ISSUE A, DATED NOVEMBER 2009.
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSIONS DO NOT INCLUDE BURRS OR MOLD FLASH. MOLD FLASH OR BURRS DOES NOT EXCEED 0.10MM.
- D) DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994.
- E) DRAWING FILE NAME: MKT-PSOF08AREV3

ON Semiconductor and  are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor
19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA
Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada
Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free
USA/Canada

Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910

Japan Customer Focus Center
Phone: 81-3-5817-1050

ON Semiconductor Website: www.onsemi.com

Order Literature: <http://www.onsemi.com/orderlit>

For additional information, please contact your local
Sales Representative